



#8A Andt.
M. Brunson
8/27/02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

KAZUHIRO SHIMIZU, ET AL.

: EXAMINER: WEISS, H.

SERIAL NO: 09/925,418

:

FILED: AUGUST 10, 2001

: GROUP ART UNIT: 2814

FOR: NON-VOLATILE
SEMICONDUCTOR MEMORY
DEVICE HAVING MEMORY
CELL ARRAY SUITABLE FOR
HIGH DENSITY AND HIGH
INTEGRATION

RECEIVED
AUG 22 2002
TECHNOLOGY CENTER 2800

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated May 17, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend Claims 1, 5, 6, 9, 10, and 13 as shown in clean form below.¹

Sub
B1
A

1. (Amended) A non-volatile semiconductor memory device comprising:
a semiconductor body of a first conductivity type;
first and second semiconductor regions of a second conductivity type, formed apart
from each other on the semiconductor body;

¹A marked-up copy of the amended portion of the claims is attached hereto.